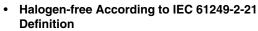


BSS84(Z)-VB Datasheet P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	V _{GS(th)} (V)	I _D (mA)			
- 60	3 at V _{GS} = - 10 V	- 1 to - 3	-500			

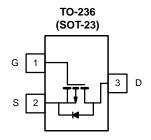
FEATURES

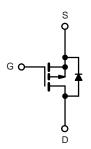




RoH:

- TrenchFET[®] Power MOSFET
- · High-Side Switching
- Low On-Resistance: 3 $\,\Omega\,$
- Low Threshold: 2 V (typ.)
- Fast Swtiching Speed: 20 ns (typ.)
- Low Input Capacitance: 20 pF (typ.)
- Compliant to RoHS Directive 2002/95/EC





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	- 60	V		
Gate-Source Voltage		V _{GS}	± 20	V		
Outline Date Outline	T _A = 25 °C	I _D	- 500	mA		
Continuous Drain Current ^a	T _A = 100 °C		- 350			
Pulsed Drain Current ^b		I _{DM}	-1500			
Davier Dissingtion 8	T _A = 25 °C	P _D	460	mW		
Power Dissipation ^a	T _A = 100 °C		240			
Maximum Junction-to-Ambient ^a	•	R _{thJA}	350	°C/W		
Operating Junction and Storage Temperature Range		T _{J,} T _{stg}	- 55 to 150	°C		

Notes:

- a. Surface mounted on FR4 board.
- b. Pulse width limited by maximum junction temperature.

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			Limits				
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -10 \mu\text{A}$	- 60			V	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	ľ	
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 10	μΑ	
Gate-Body Leakage		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$			± 200	nA	
	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			± 500		
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			± 100		
Zava Cata Valtaga Dvain Current		V _{DS} = - 60 V, V _{GS} = 0 V			- 25		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 85 °C			- 250	1	
On-State Drain Current ^a	,	V _{GS} = - 10 V, V _{DS} = - 4.5 V - 50				mA	
	I _{D(on)}	V _{GS} = - 10 V, V _{DS} = - 10 V	- 600				
Drain-Source On-Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 25 mA		4			
		V _{GS} = - 10 V, I _D = - 100 mA		3		Ω	
		V _{GS} = - 10 V, I _D = - 100 mA, T _J =125 °C		9			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 100 mA	80			mS	
Diode Forward Voltage	V _{SD}	I _S = - 100 mA, V _{GS} = 0 V			- 1.4	٧	
Dynamic							
Total Gate Charge	Qg			2.0		nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -15 \text{ V}$ $I_{D} \cong -100 \text{ mA}$		1.2			
Gate-Drain Charge	Q _{gd}	10 = - 100 mA		0.8			
Input Capacitance	C _{iss}			23		pF	
Output Capacitance	C _{oss}	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}$ f = 1 MHz		10			
Reverse Transfer Capacitance	C _{rss}	1 – 1 1411 12		5			
Switching ^b	•		•				
Turn-On Time	t _{d(on)}	$V_{DD} = -25 \text{ V}, R_{L} = 150 \Omega$		20		ns	
Turn-Off Time	t _{d(off)}	$I_D \cong$ - 200 mA, $V_{GEN} =$ - 10 V, $R_g =$ 10 Ω		35			

Notes:

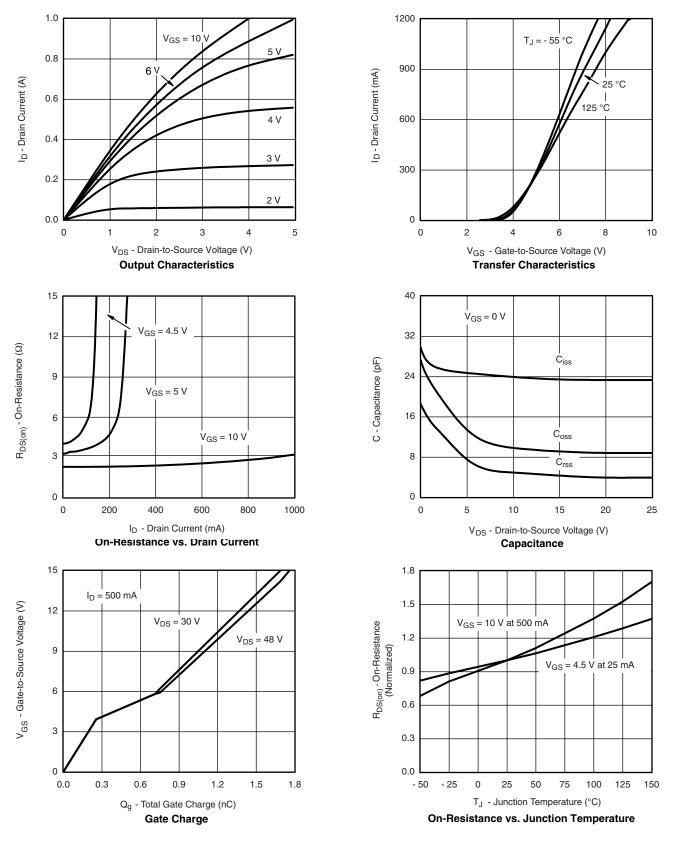
- a. Pulse test: PW \leq 300 μs duty cycle \leq 2 %.
- b. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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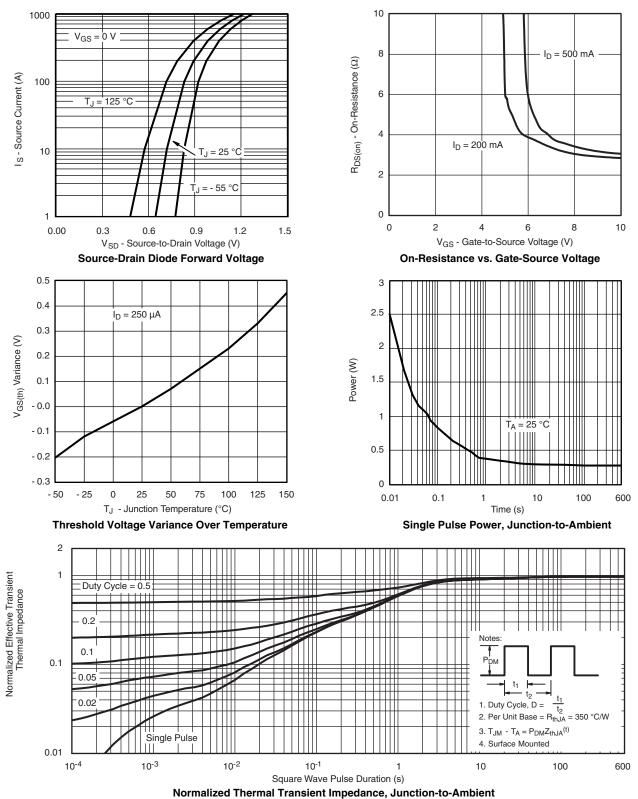
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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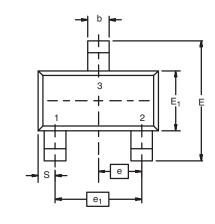
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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SOT-23 (TO-236): 3-LEAD







Dim	MILLIMETERS		INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	

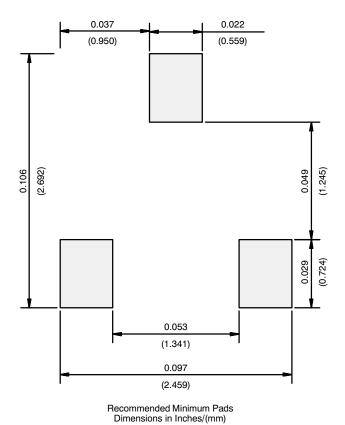
ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

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RECOMMENDED MINIMUM PADS FOR SOT-23



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